

IRF7750

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (< 1.1mm)
- Available in Tape & Reel



$V_{DS} = -20V$
$R_{DS(on)} = 0.030\Omega$

Description

HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design, that International Rectifier is well known for, provides the designer with an extremely efficient and reliable device for battery and load management.

The TSSOP-8 package has 45% less footprint area than the standard SO-8. This makes the TSSOP-8 an ideal device for applications where printed circuit board space is at a premium. The low profile (<1.1mm) allows it to fit easily into extremely thin environments such as portable electronics and PCMCIA cards.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	± 4.7	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V$	± 3.8	
I_{DM}	Pulsed Drain Current ①	± 38	
$P_D @ T_C = 25^\circ C$	Power Dissipation	1.0	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	0.64	
	Linear Derating Factor	0.008	
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	$^\circ C$

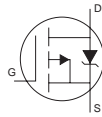
Thermal Resistance

	Parameter	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ③	125	$^\circ C/W$

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.012	—	V/°C	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.030	Ω	$V_{GS} = -4.5V, I_D = -4.7A$ ②
		—	—	0.055		$V_{GS} = -2.5V, I_D = -3.8A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.45	—	-1.2	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	11	—	—	S	$V_{DS} = -10V, I_D = -4.7A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -20V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -16V, V_{GS} = 0V, T_J = 70^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	26	39	nC	$I_D = -4.7A$
Q_{gs}	Gate-to-Source Charge	—	3.9	5.8		$V_{DS} = -16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.0	12		$V_{GS} = -5.0V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	15	—	ns	$V_{DD} = -10V$
t_r	Rise Time	—	54	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	180	—		$R_D = 10\Omega$
t_f	Fall Time	—	210	—		$R_G = 24\Omega$ ②
C_{iss}	Input Capacitance	—	1700	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	380	—		$V_{DS} = -15V$
C_{rss}	Reverse Transfer Capacitance	—	270	—		$f = 1.0\text{MHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-38		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.0A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	26	39	ns	$T_J = 25^\circ\text{C}, I_F = -1.0A$
Q_{rr}	Reverse Recovery Charge	—	16	24	nC	$di/dt = 100A/\mu s$ ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

③ When mounted on 1 inch square copper board, $t < 10$ sec

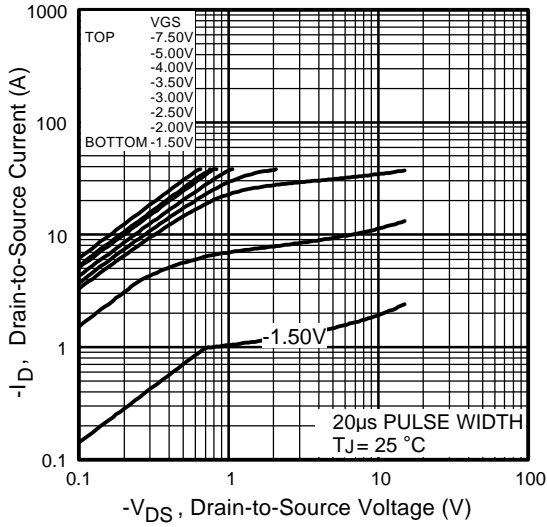


Fig 1. Typical Output Characteristics

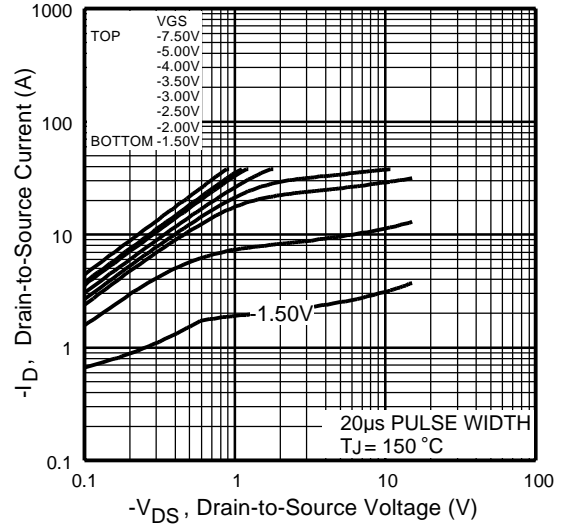


Fig 2. Typical Output Characteristics

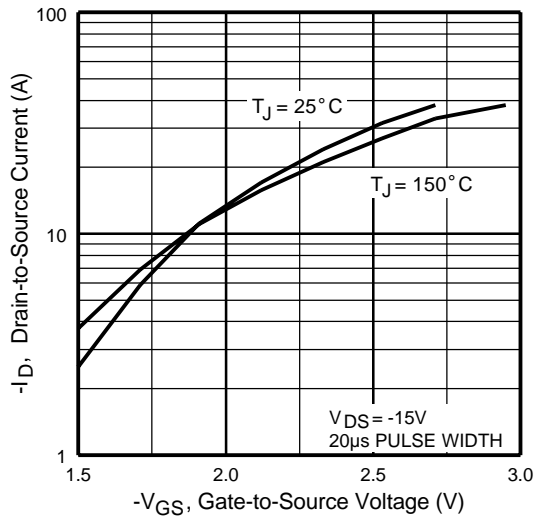


Fig 3. Typical Transfer Characteristics

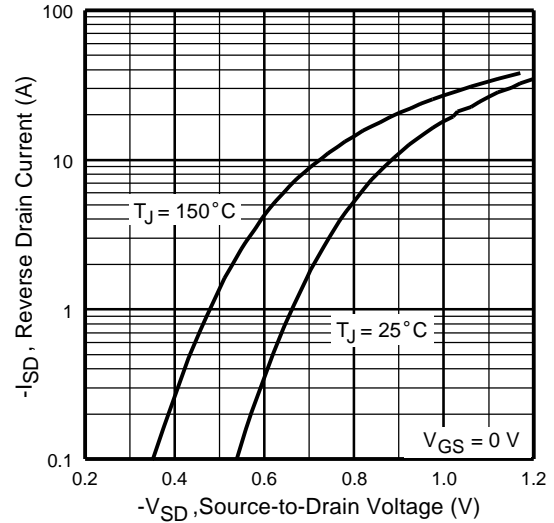


Fig 4. Typical Source-Drain Diode Forward Voltage

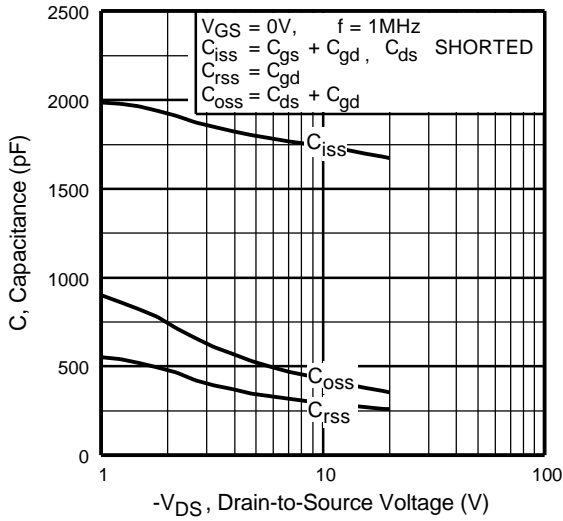


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

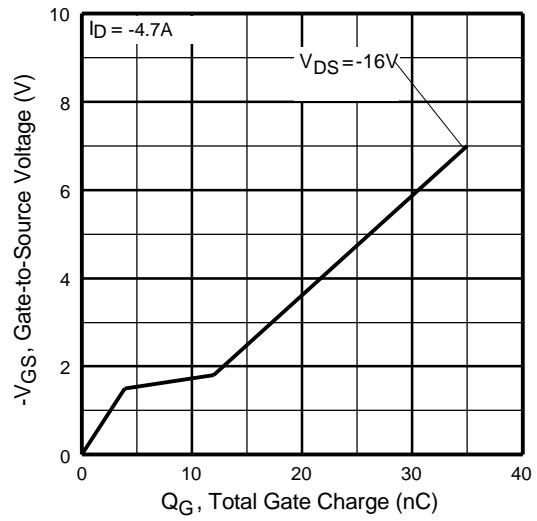


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

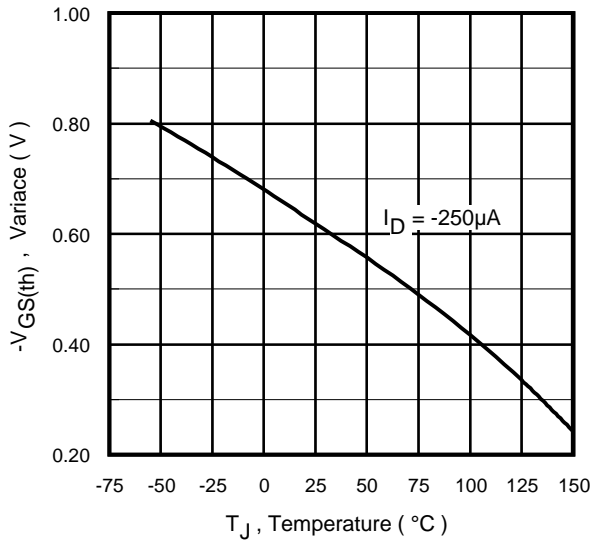


Fig 7. Threshold Voltage Vs. Temperature

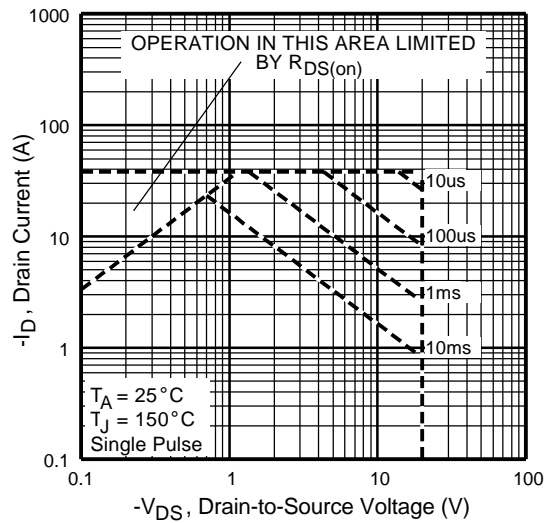


Fig 8. Maximum Safe Operating Area

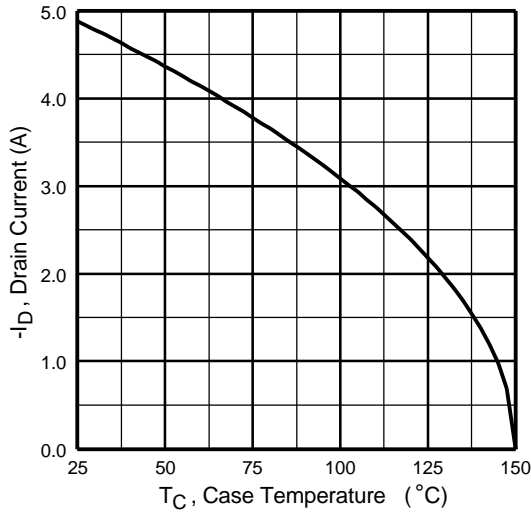


Fig 9. Maximum Drain Current Vs. Case Temperature

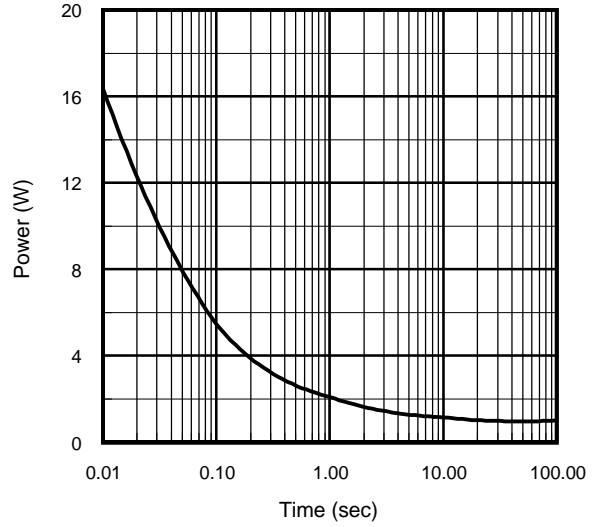


Fig 10. Typical Power Vs. Time

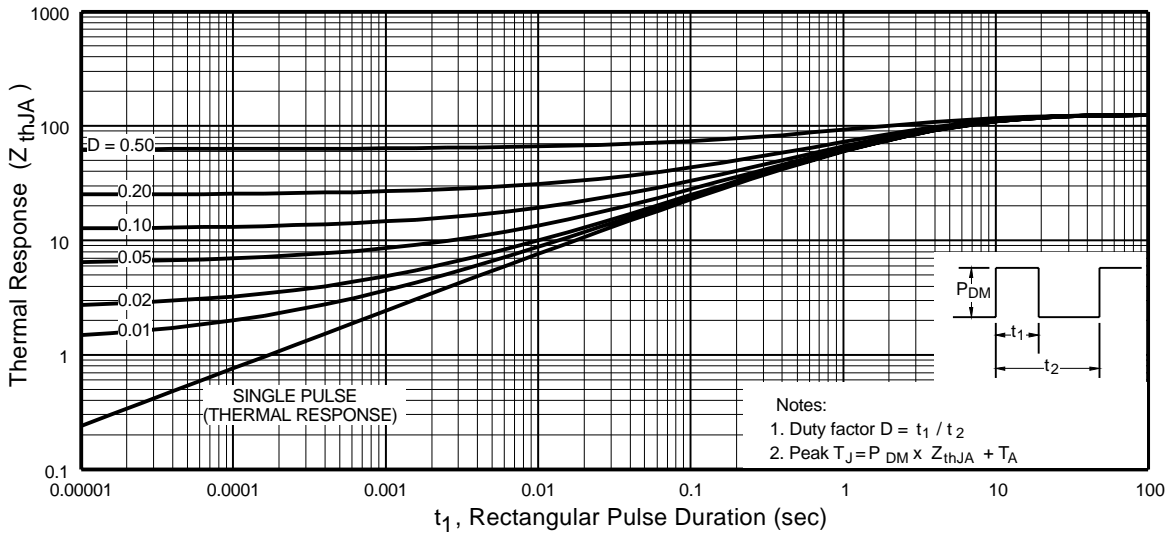


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

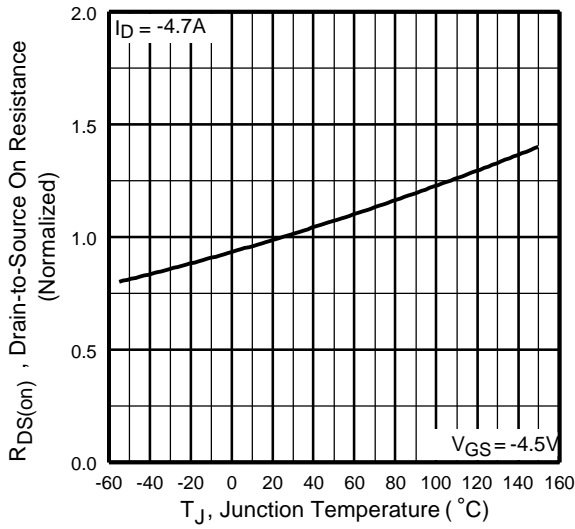


Fig 12. Normalized On-Resistance Vs. Temperature

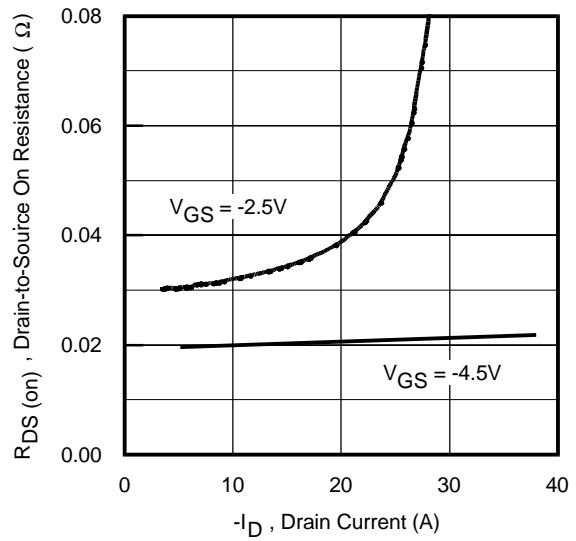


Fig 13. Typical On-Resistance Vs. Drain Current

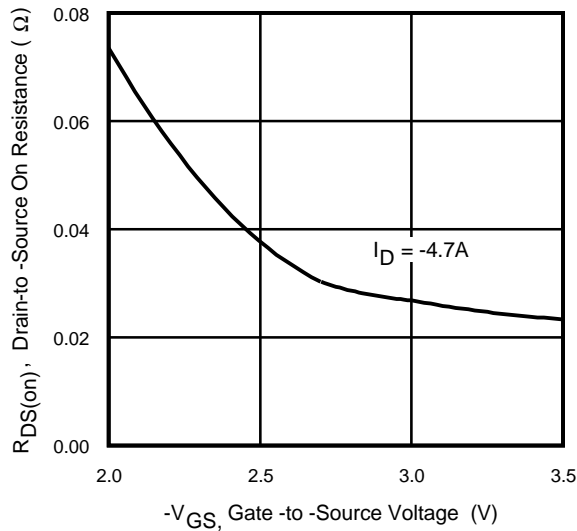
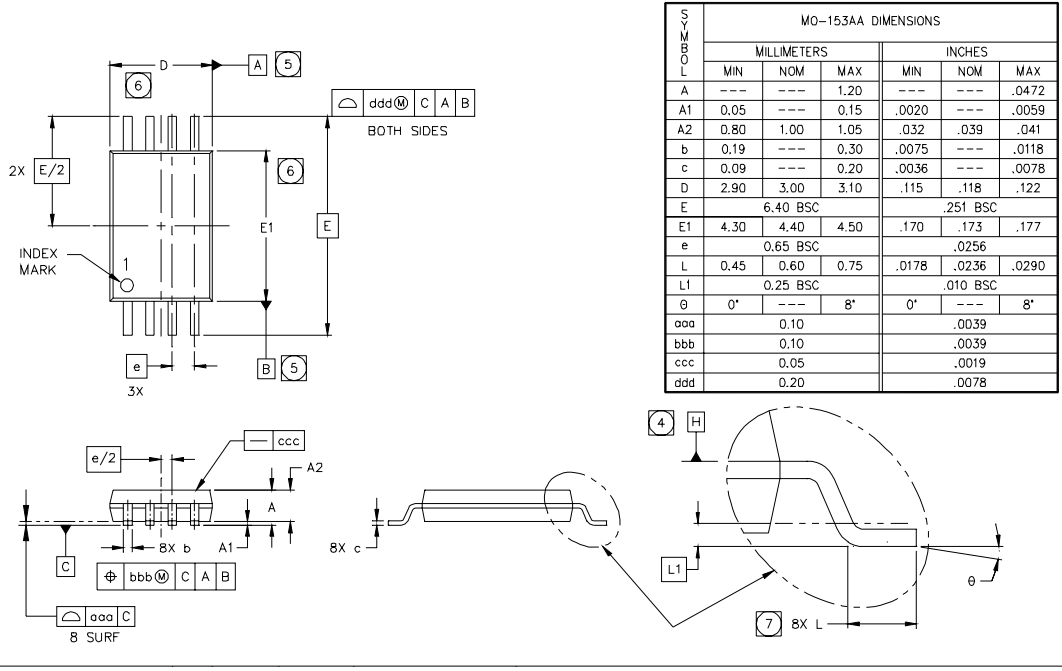
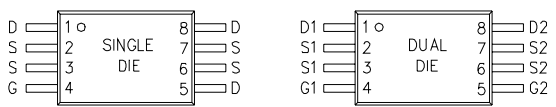


Fig 14. Typical On-Resistance Vs. Gate Voltage

TSSOP-8 Package Outline



LEAD ASSIGNMENTS



NOTES

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
2. DIMENSIONS ARE SHOWN IN MILL
- 4 DATUM PLANE H IS LOCATED AS SHOWN.
- 5 DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
- 6 DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.

WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, Tel: (310) 252-7105
IR GREAT BRITAIN: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: ++ 44 1883 732020
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 11 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo Japan 171 Tel: 81 3 3983 0086
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 838 4630
IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673, Taiwan Tel: 886-2-2377-9936
Data and specifications subject to change without notice. 5/2000